

Fig. 1

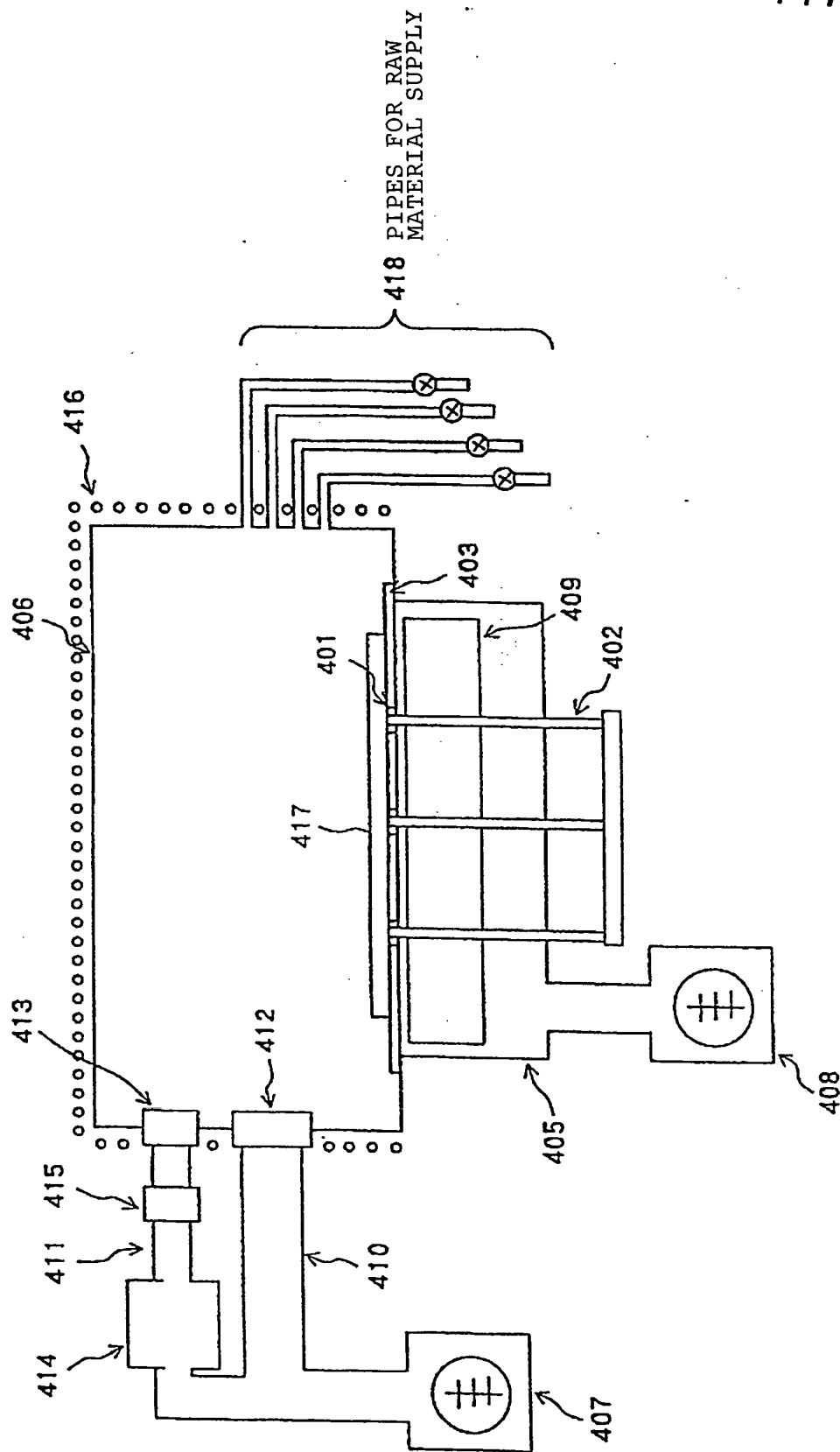


Fig. 2

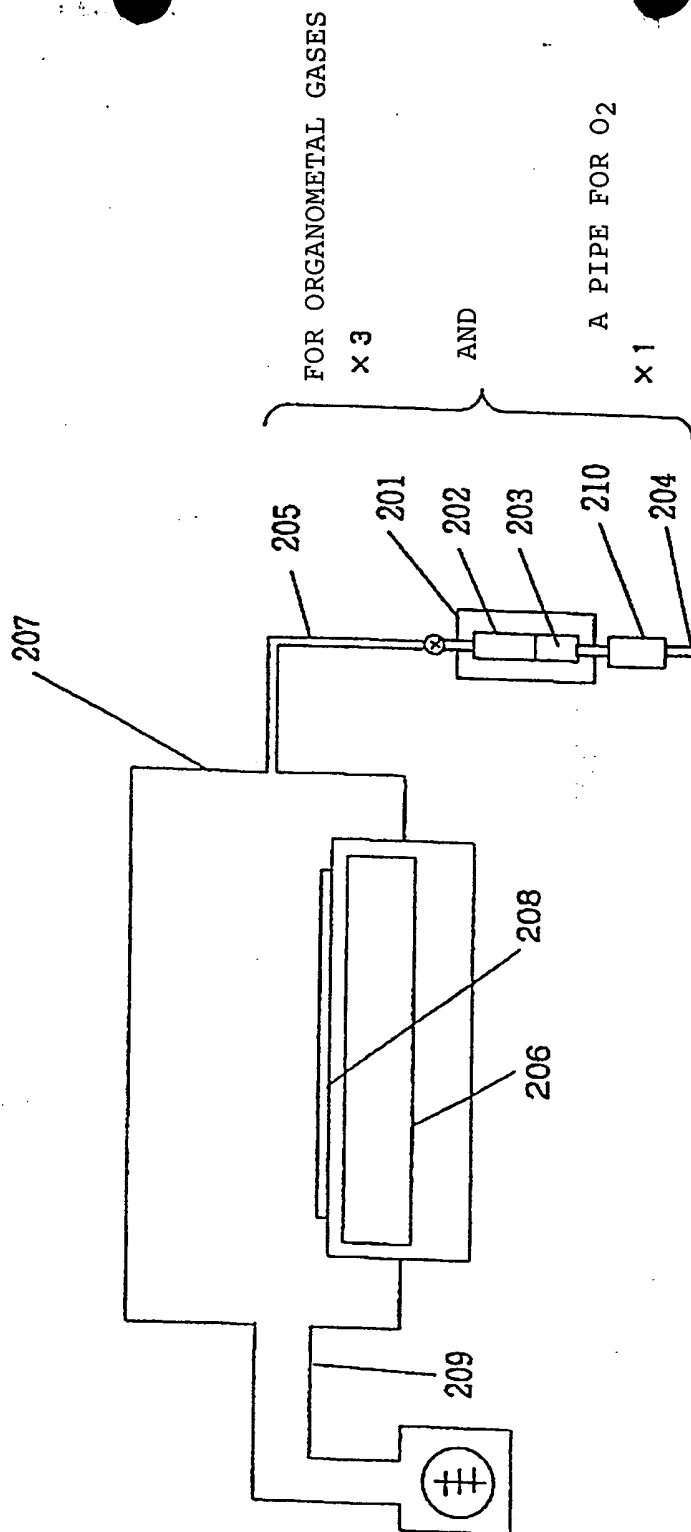


Fig. 3

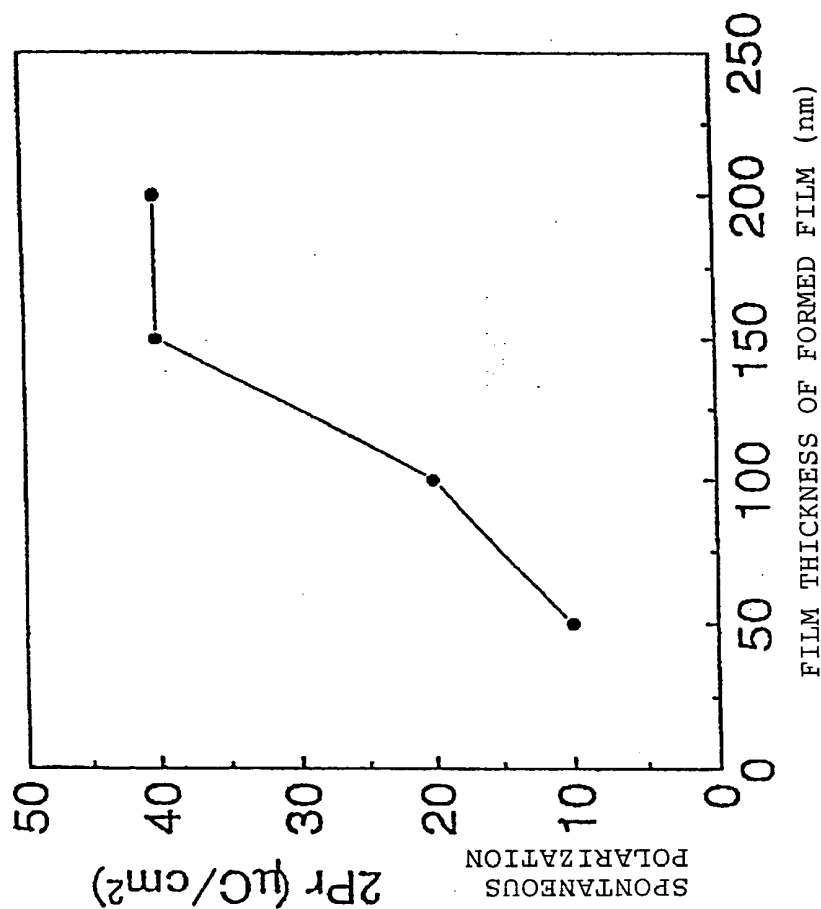


Fig. 4

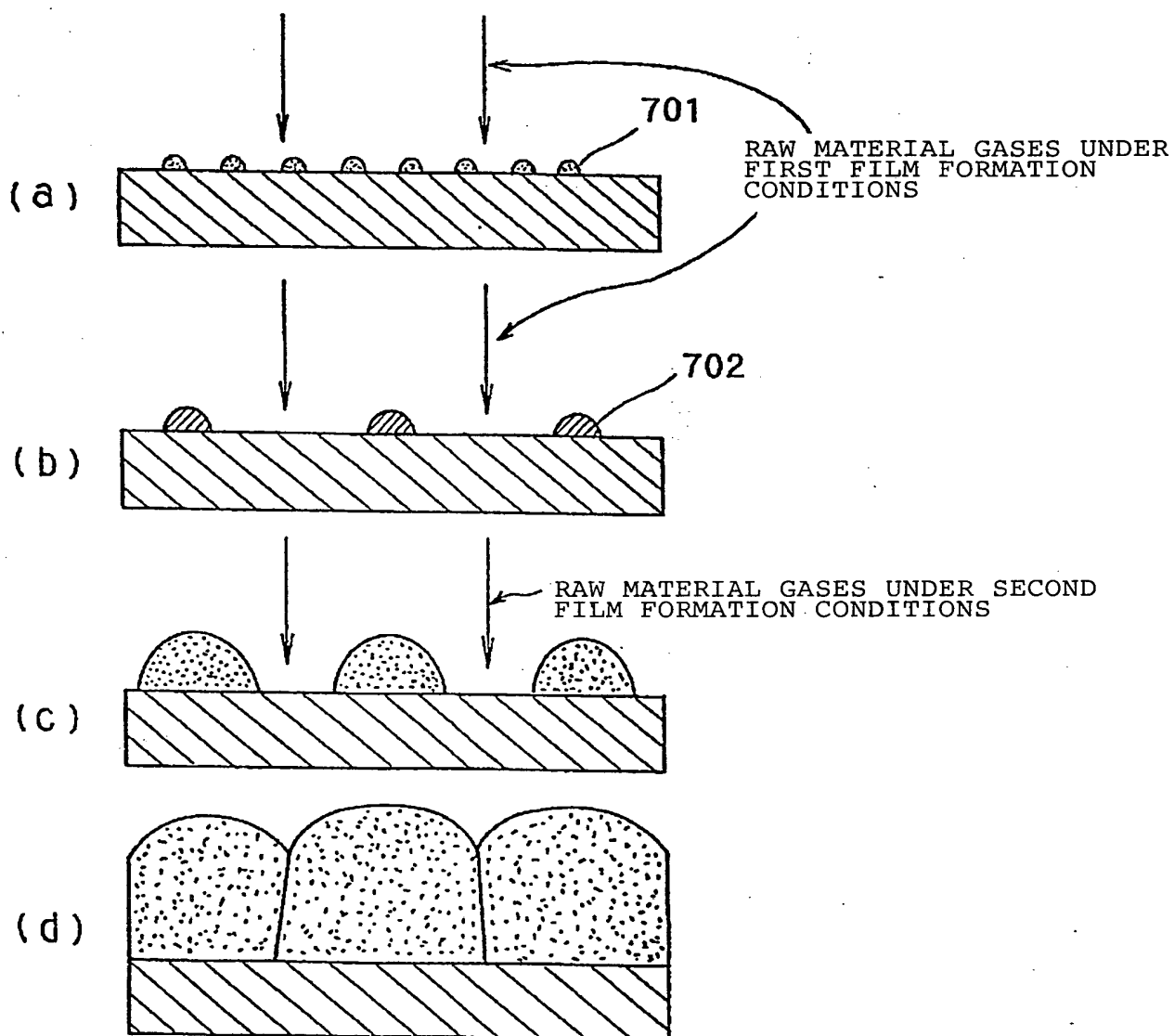


Fig. 5

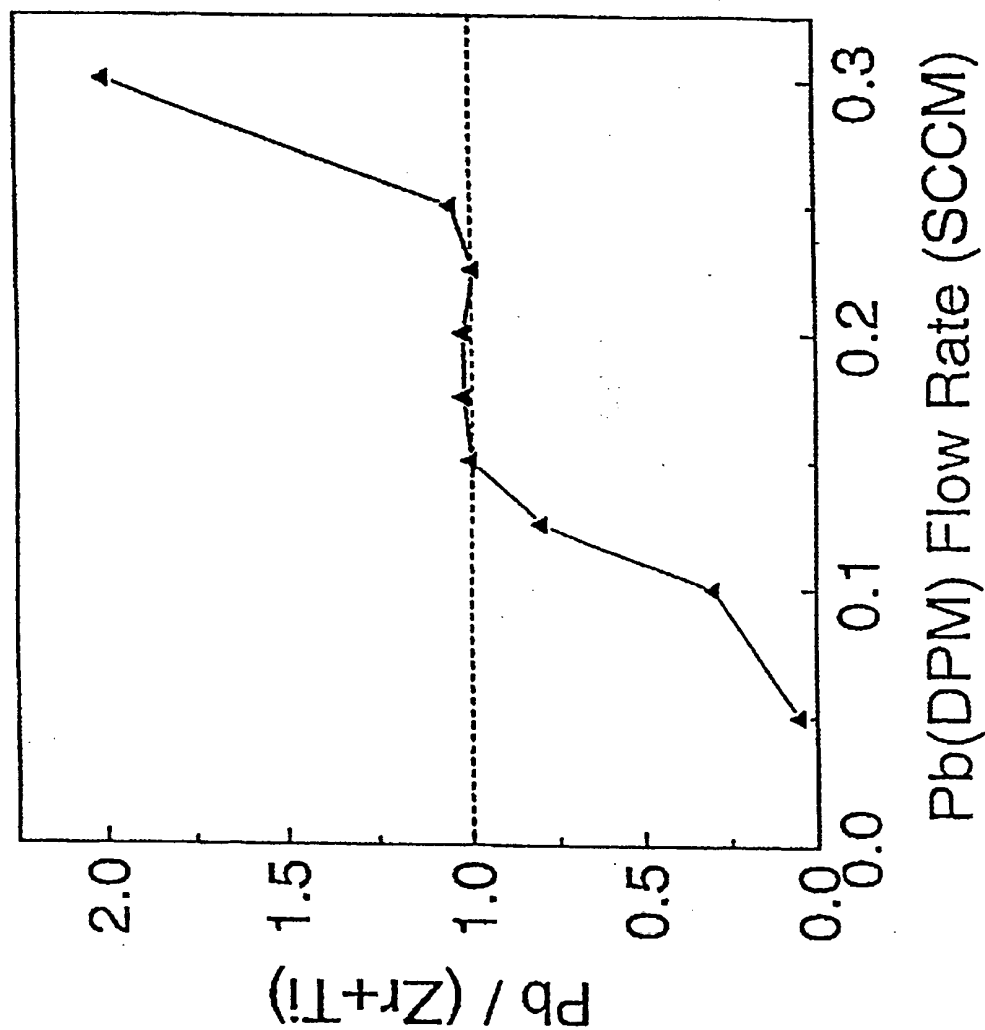


Fig. 6

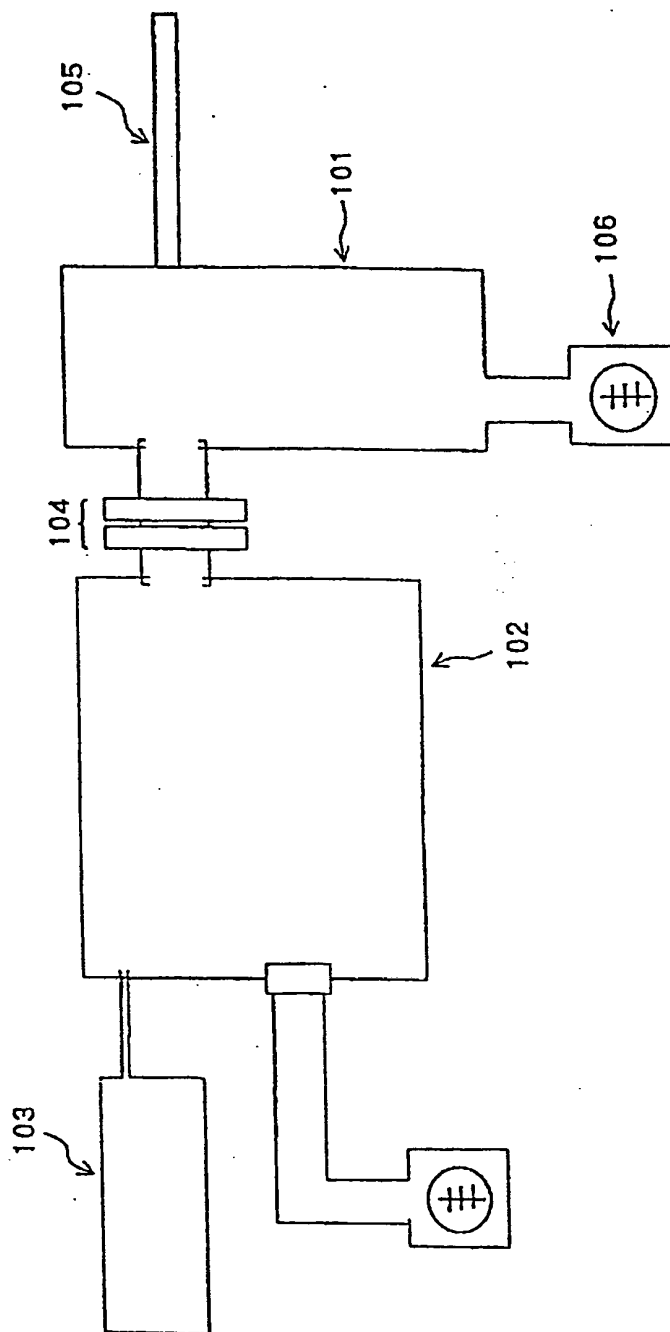


Fig. 7

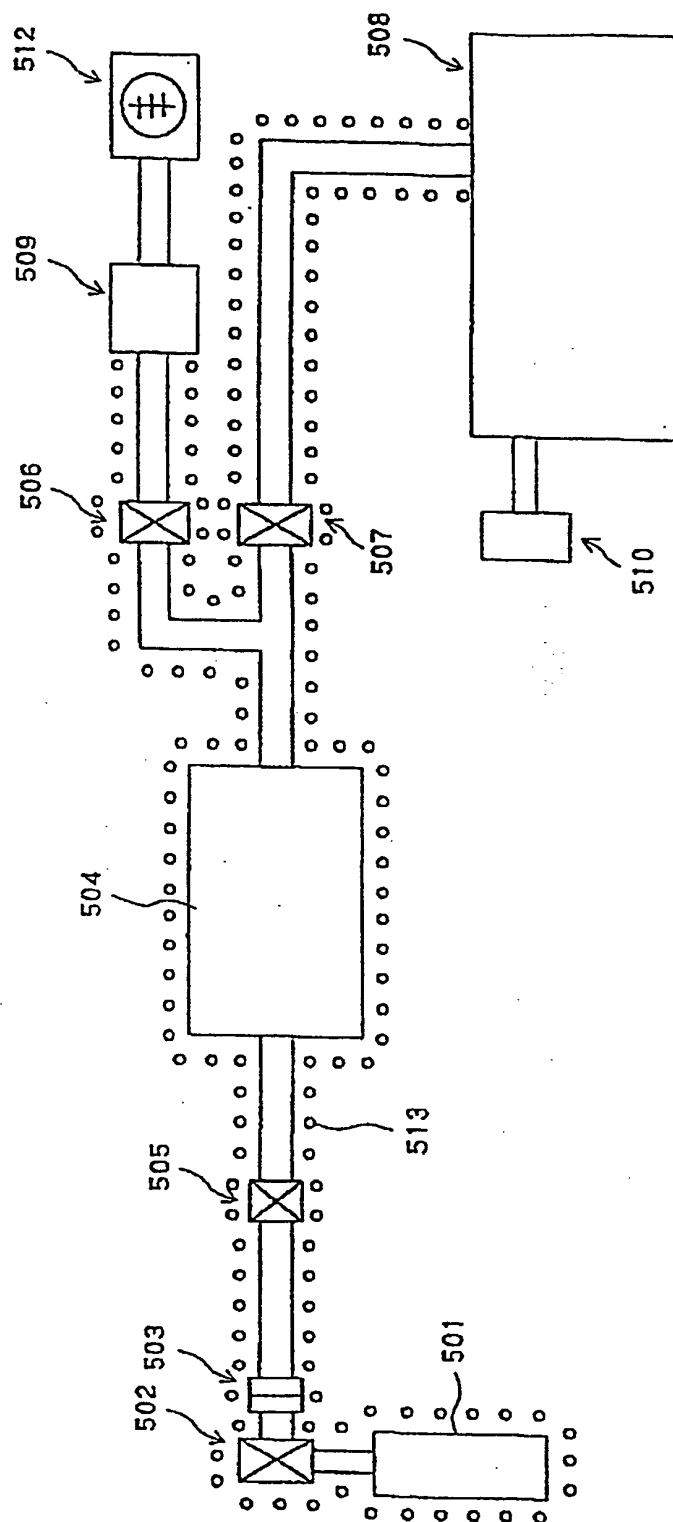
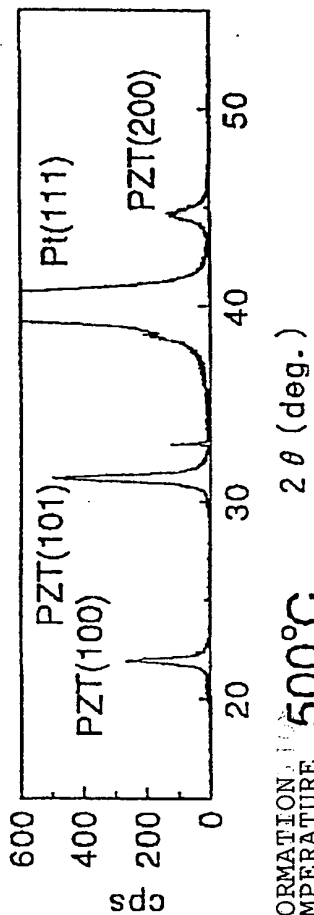


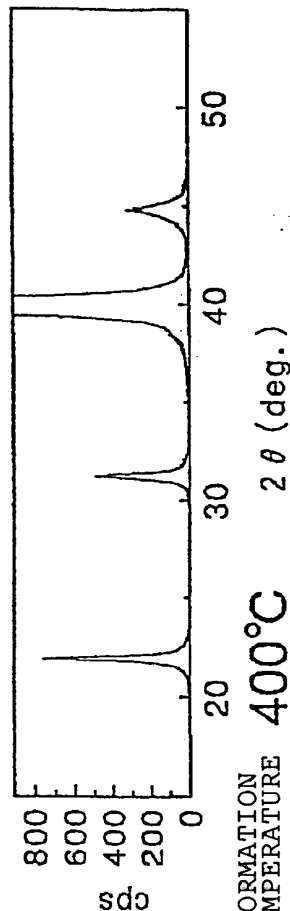
Fig. 8

FILM FORMATION TEMPERATURE

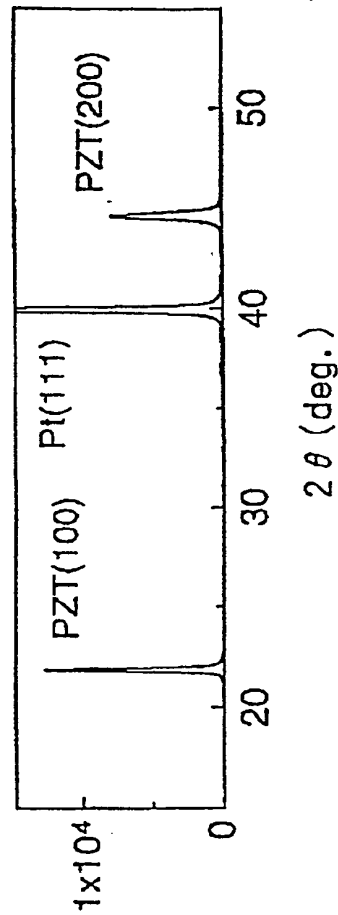
600°C



FILM FORMATION TEMPERATURE 500°C



FILM FORMATION TEMPERATURE 400°C





T06270-102444250

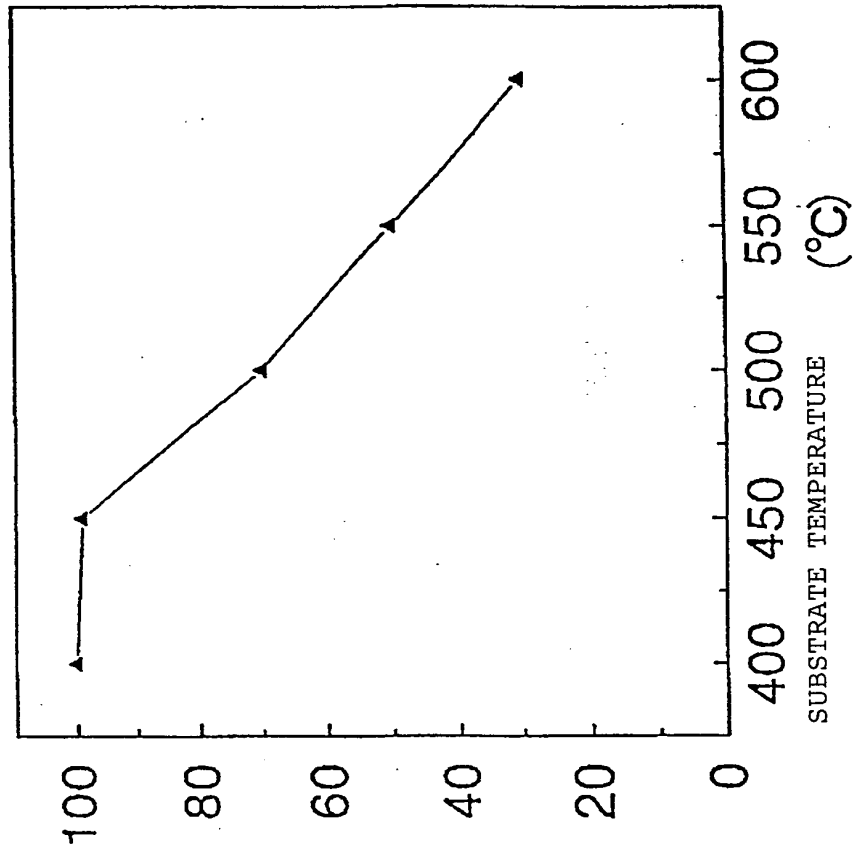


Fig. 9

RATIO (%) OF (100) CRYSTAL GRAIN

Fig. 10

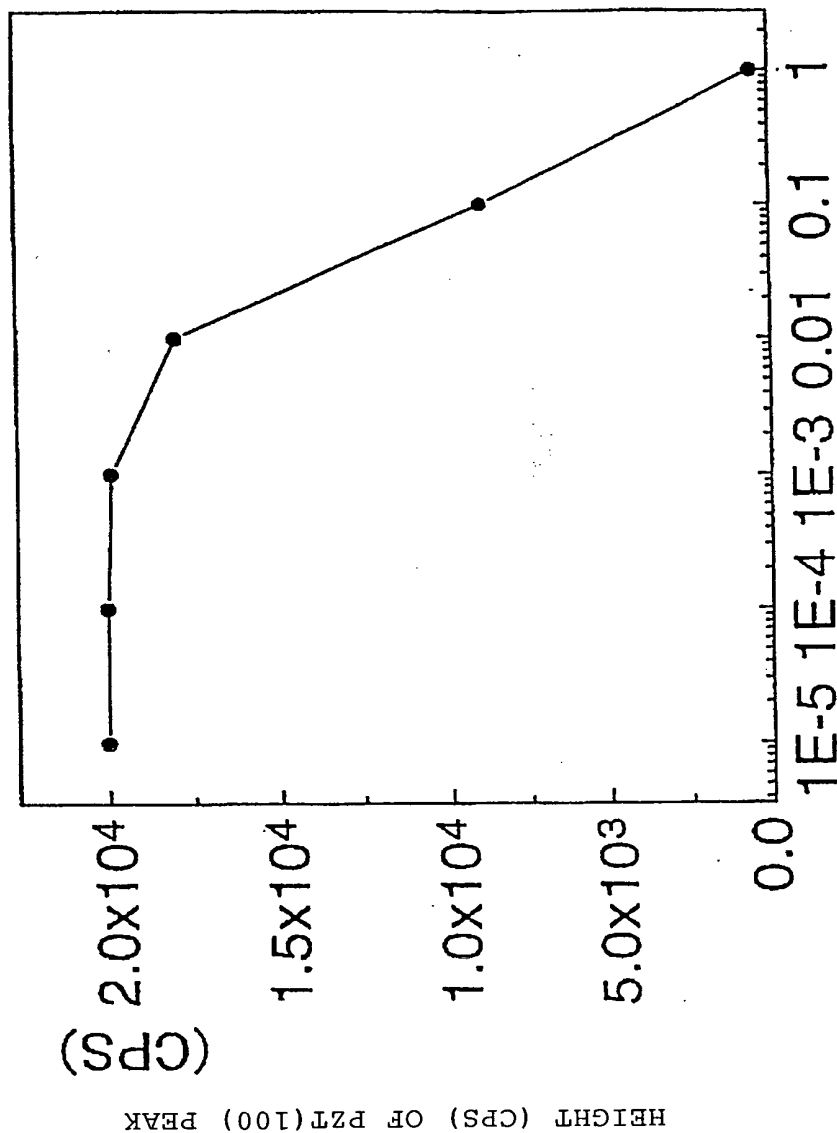
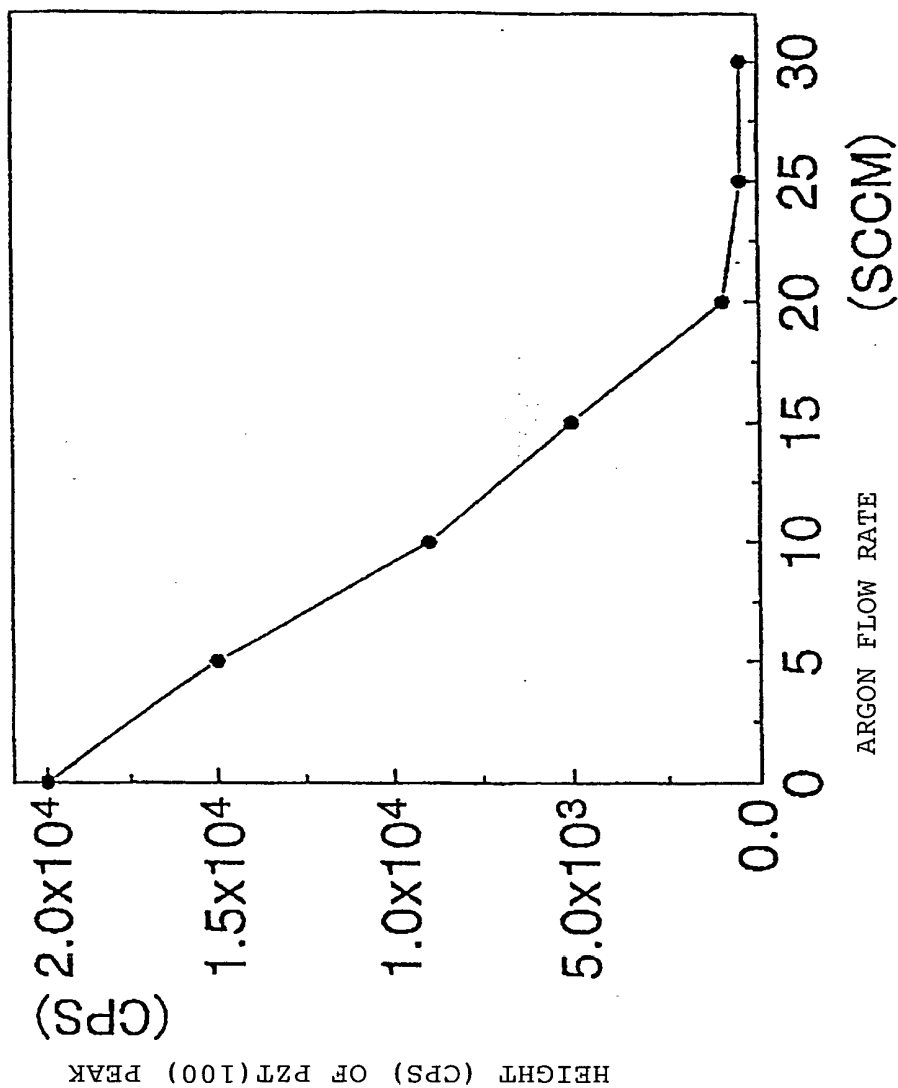


Fig. 11



FORMED

Fig. 12

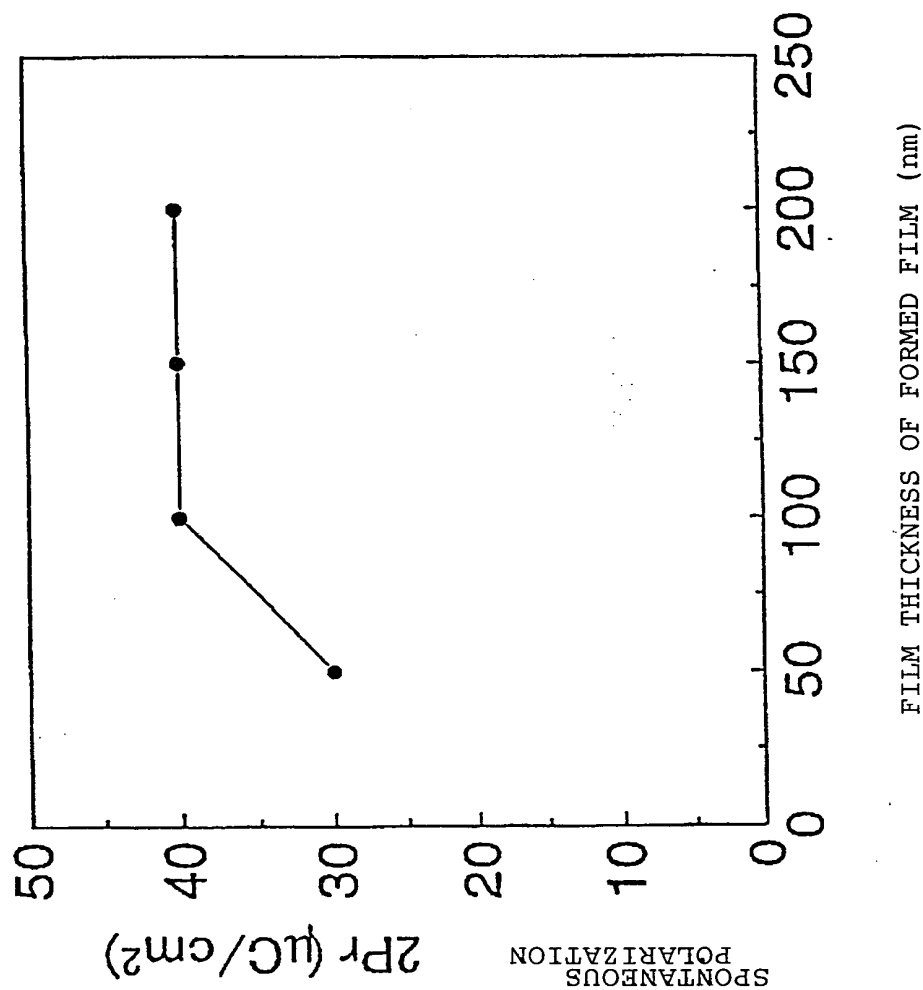


Fig. 13

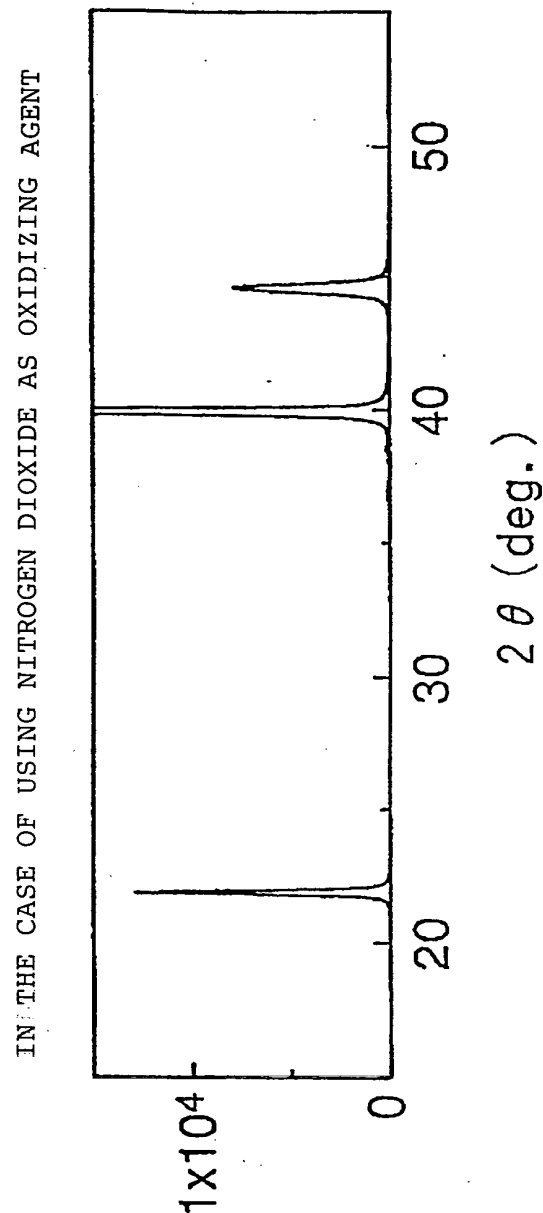
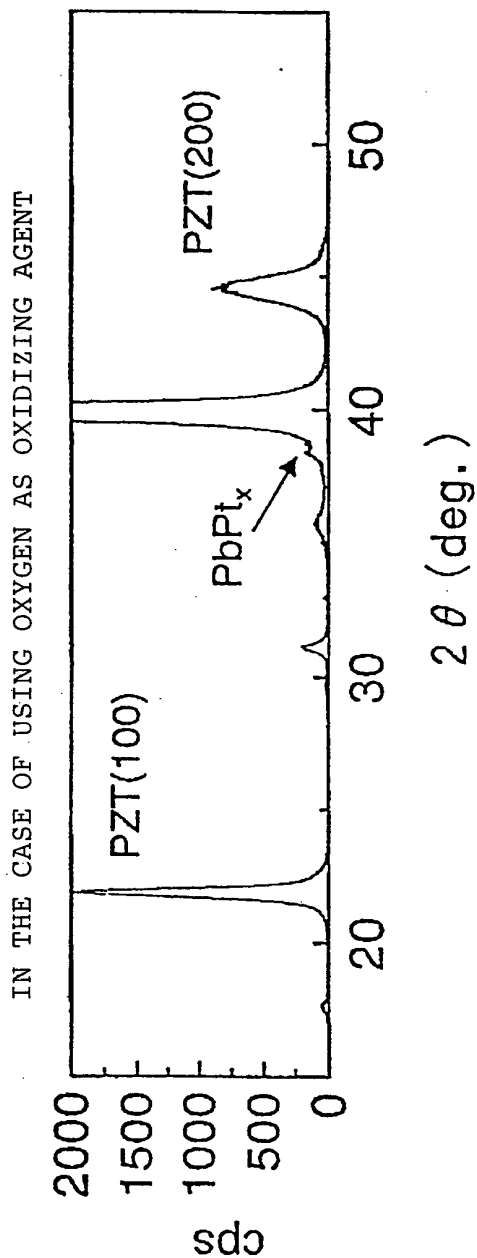


Fig. 14

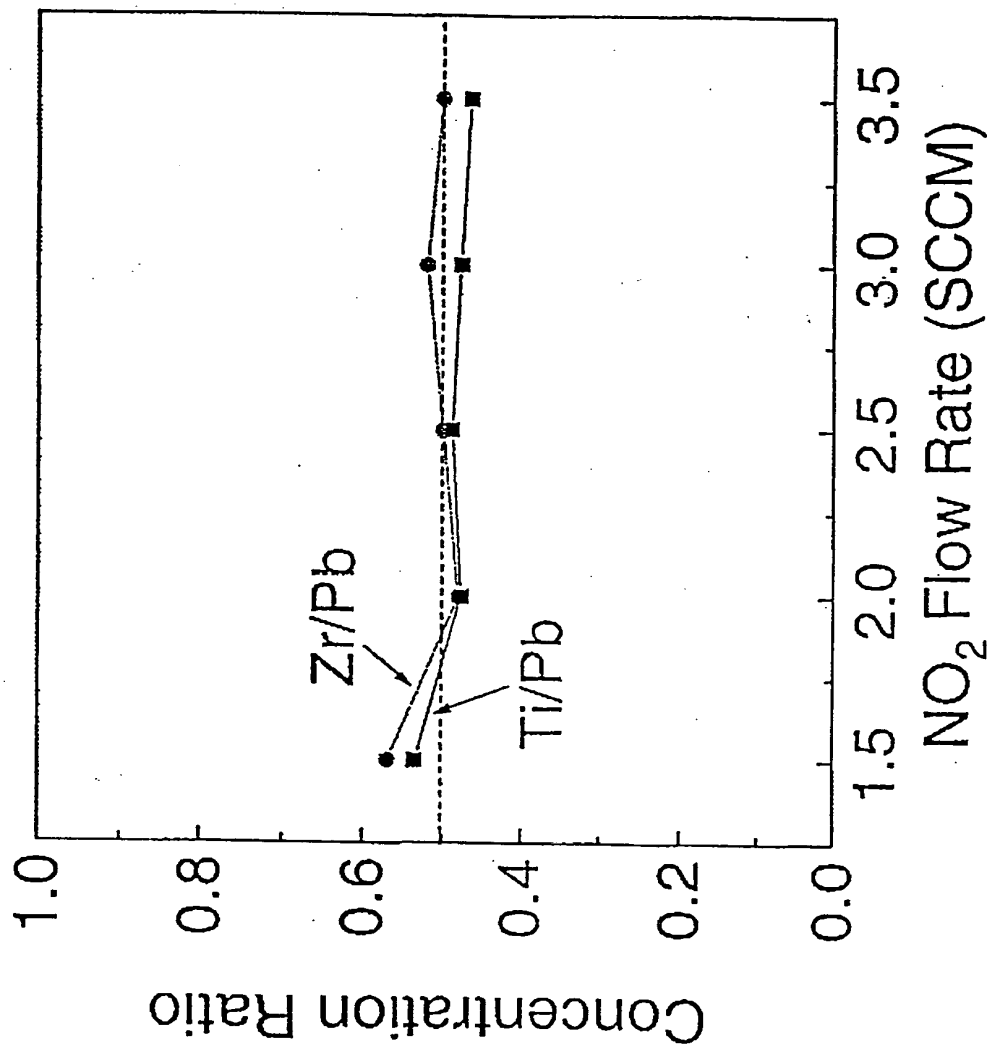
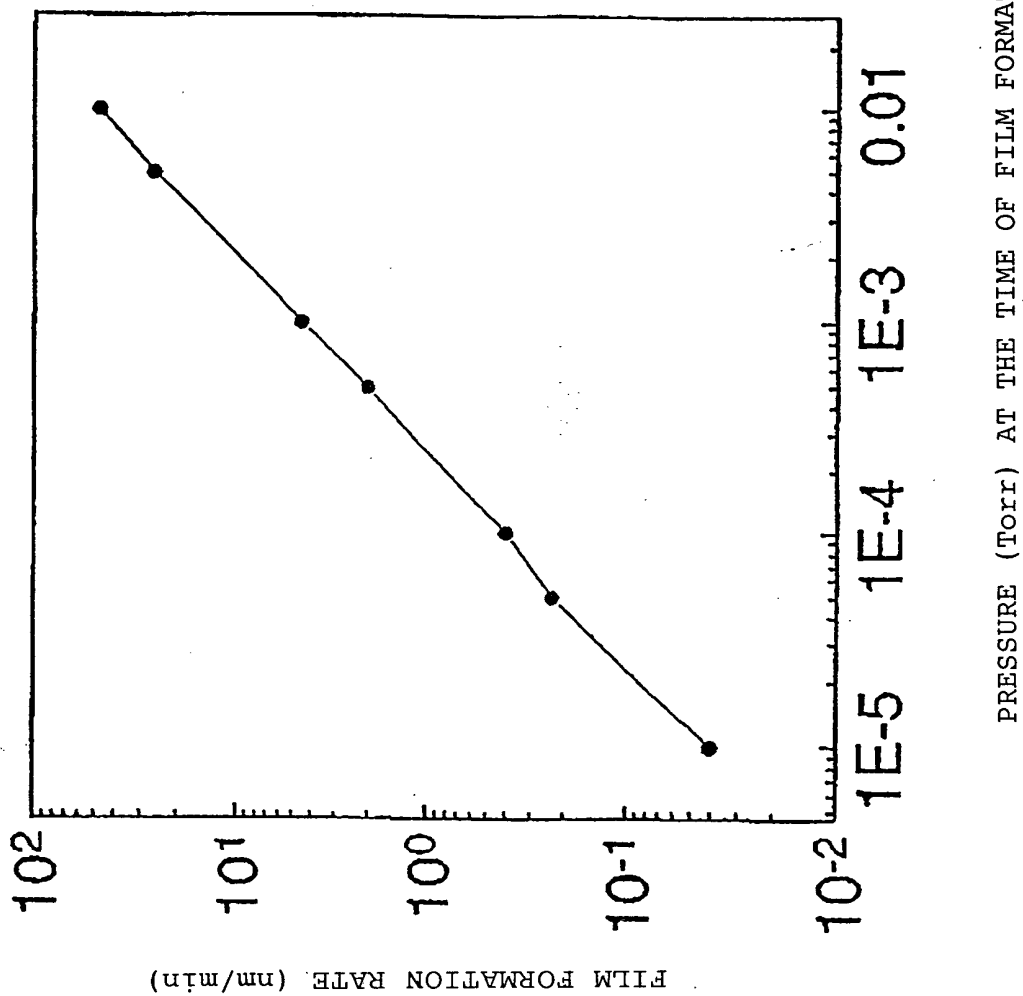
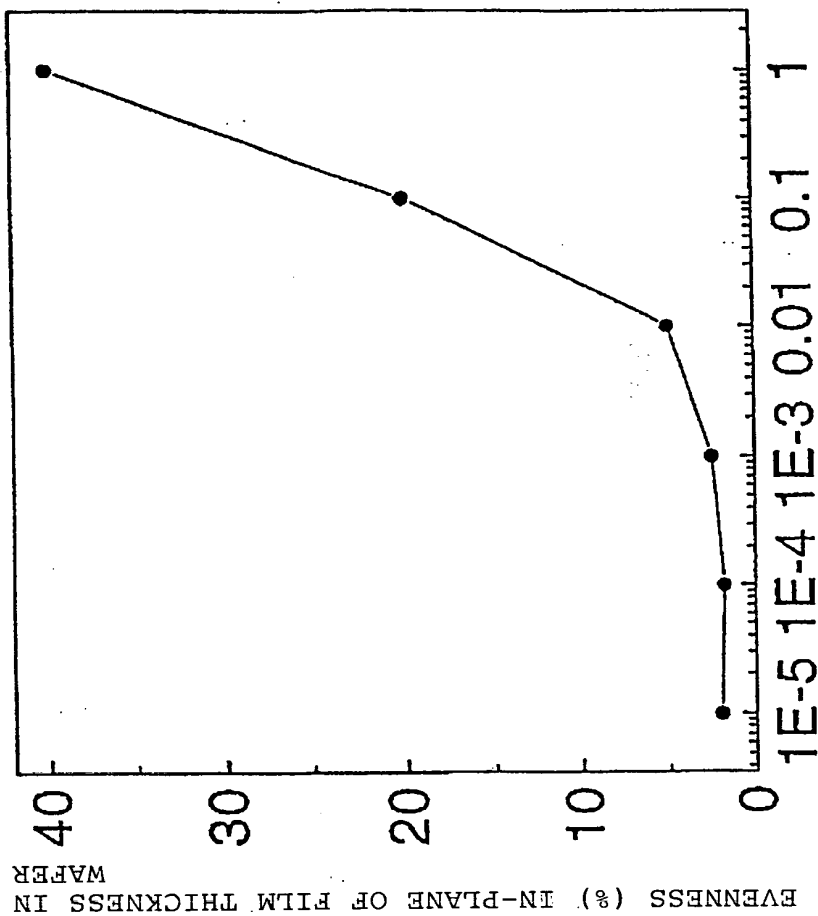


Fig. 15



T05210-10444600

Fig. 16





FOOTNOTED

Fig. 17

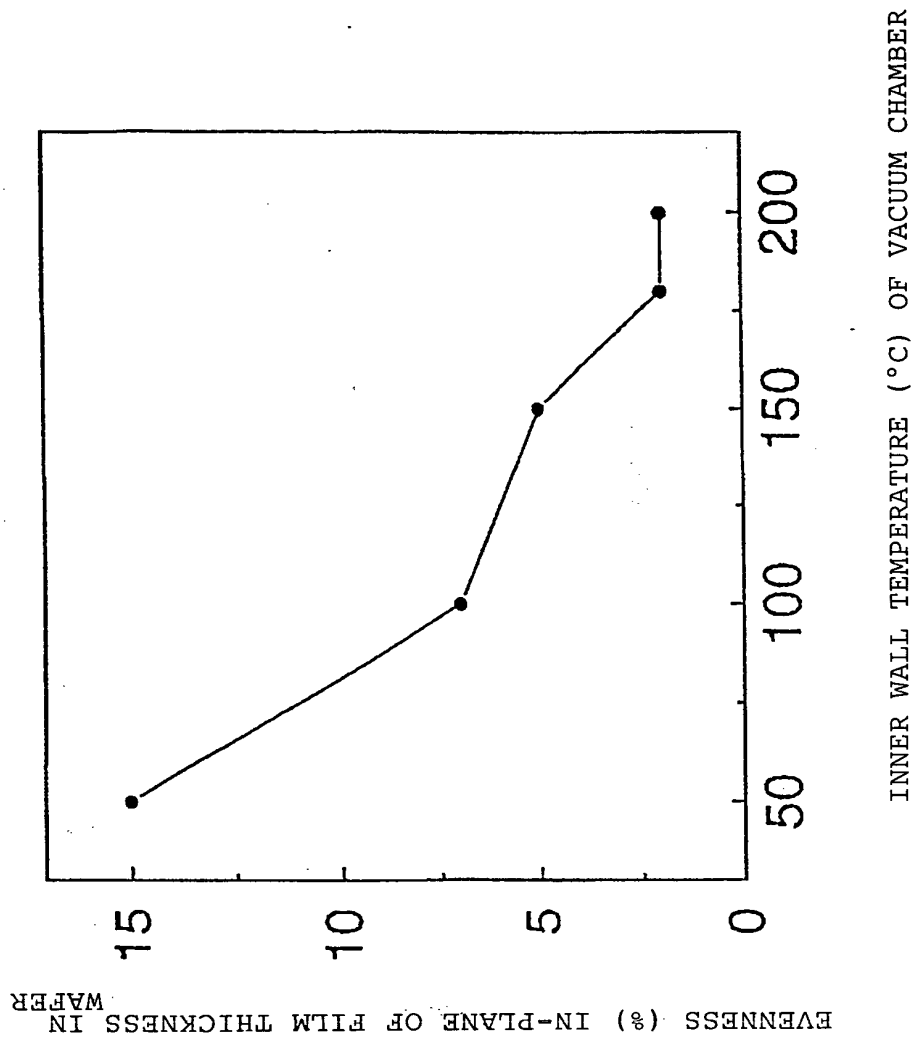


Fig. 18

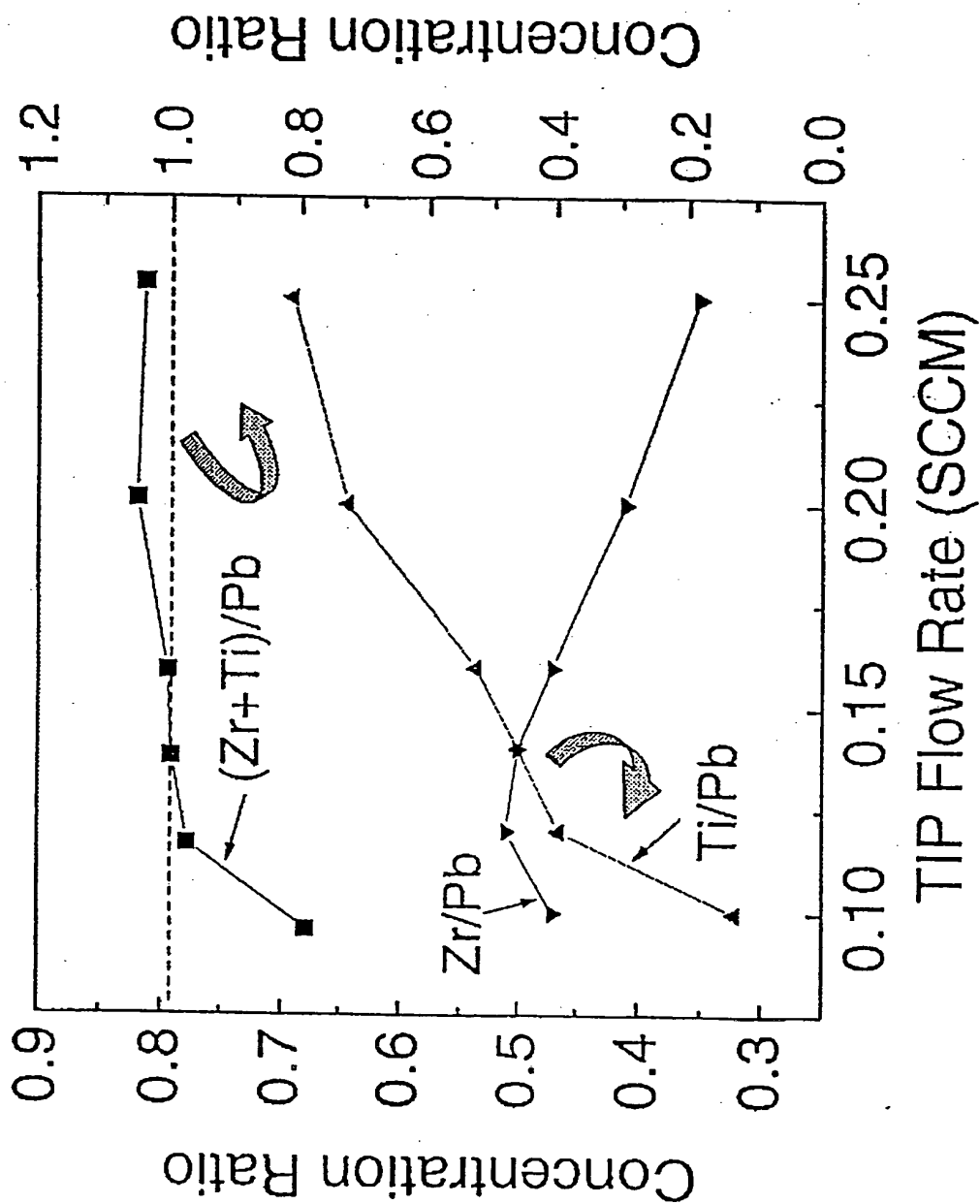


Fig. 19

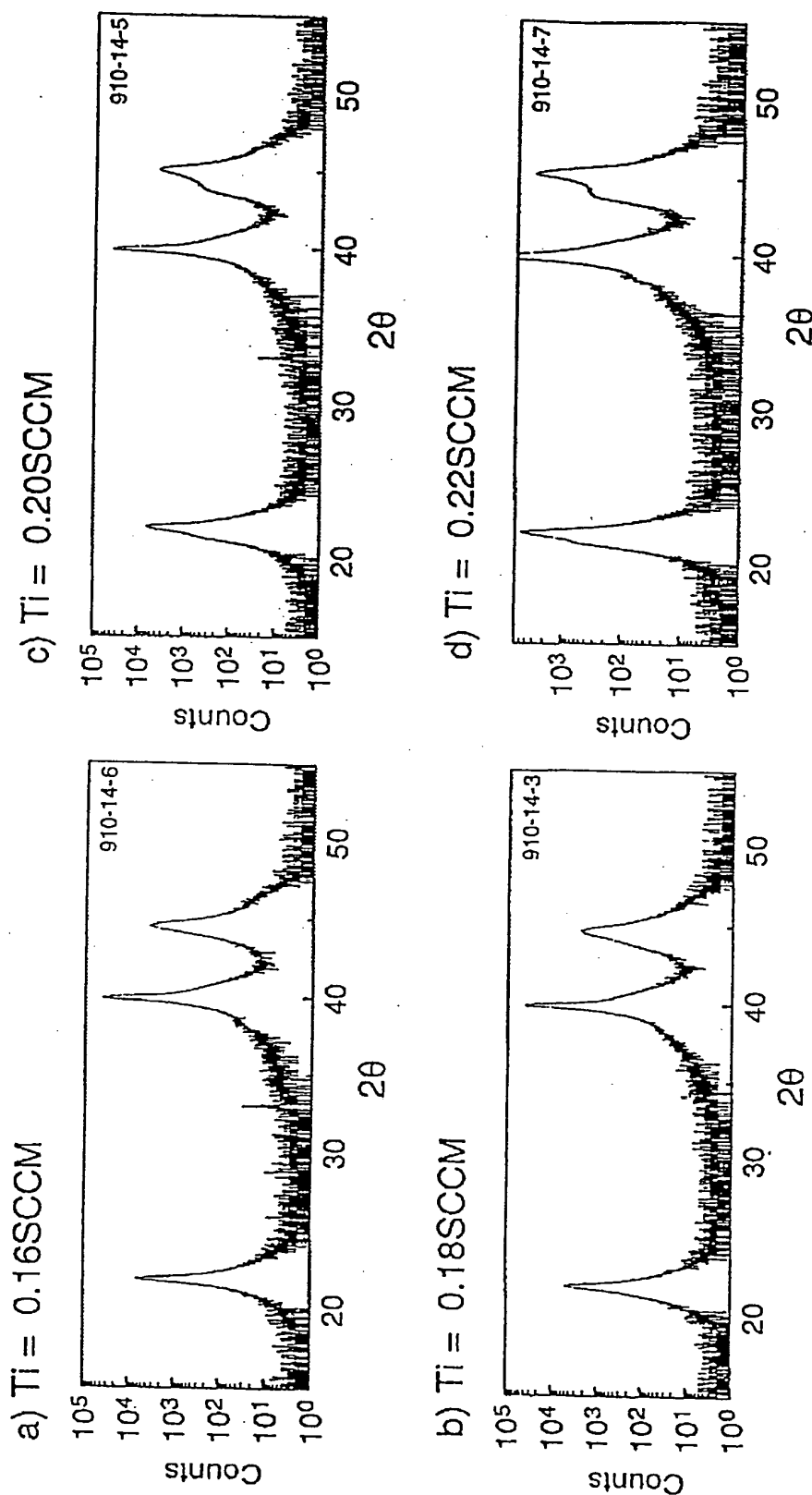


Fig. 20

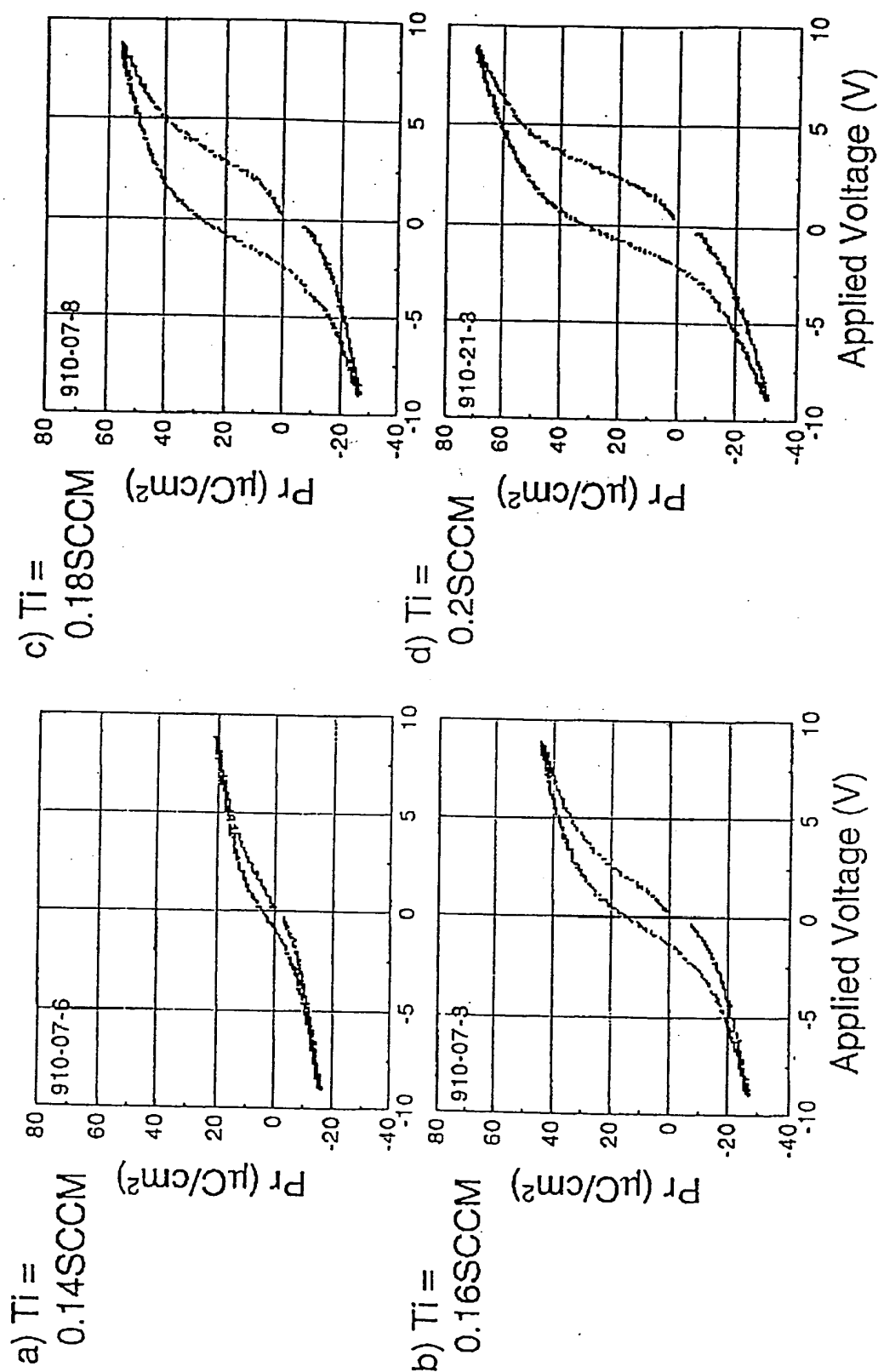
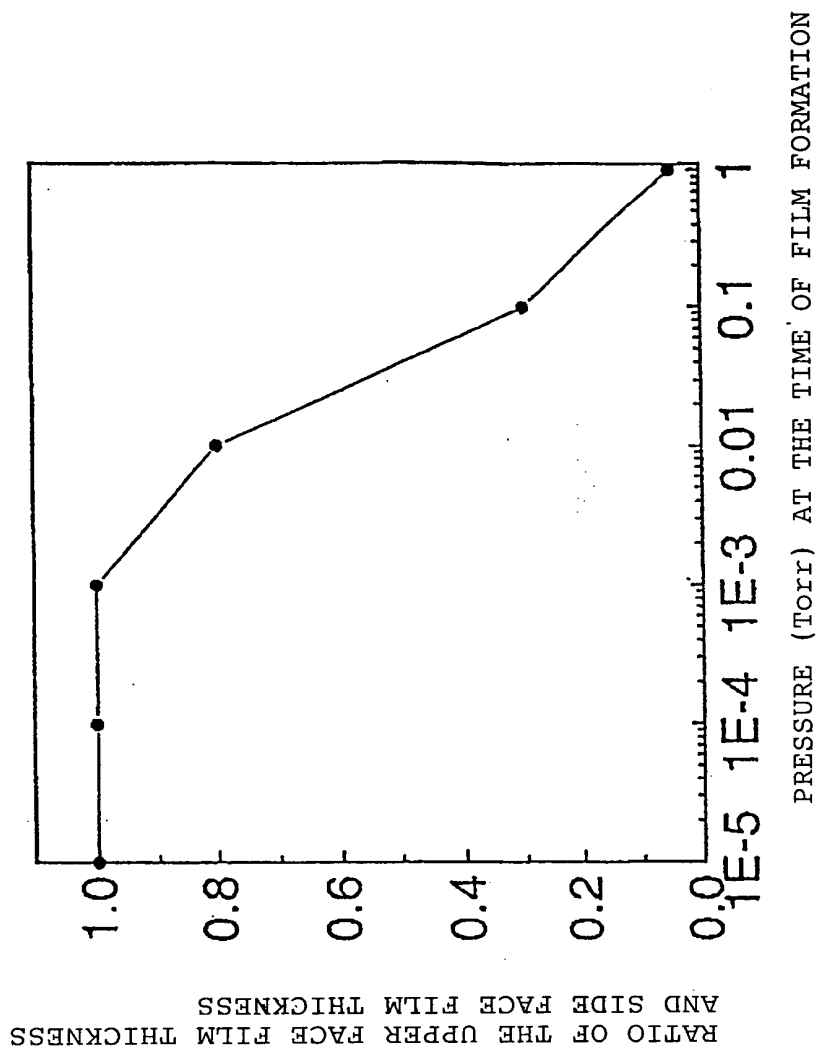
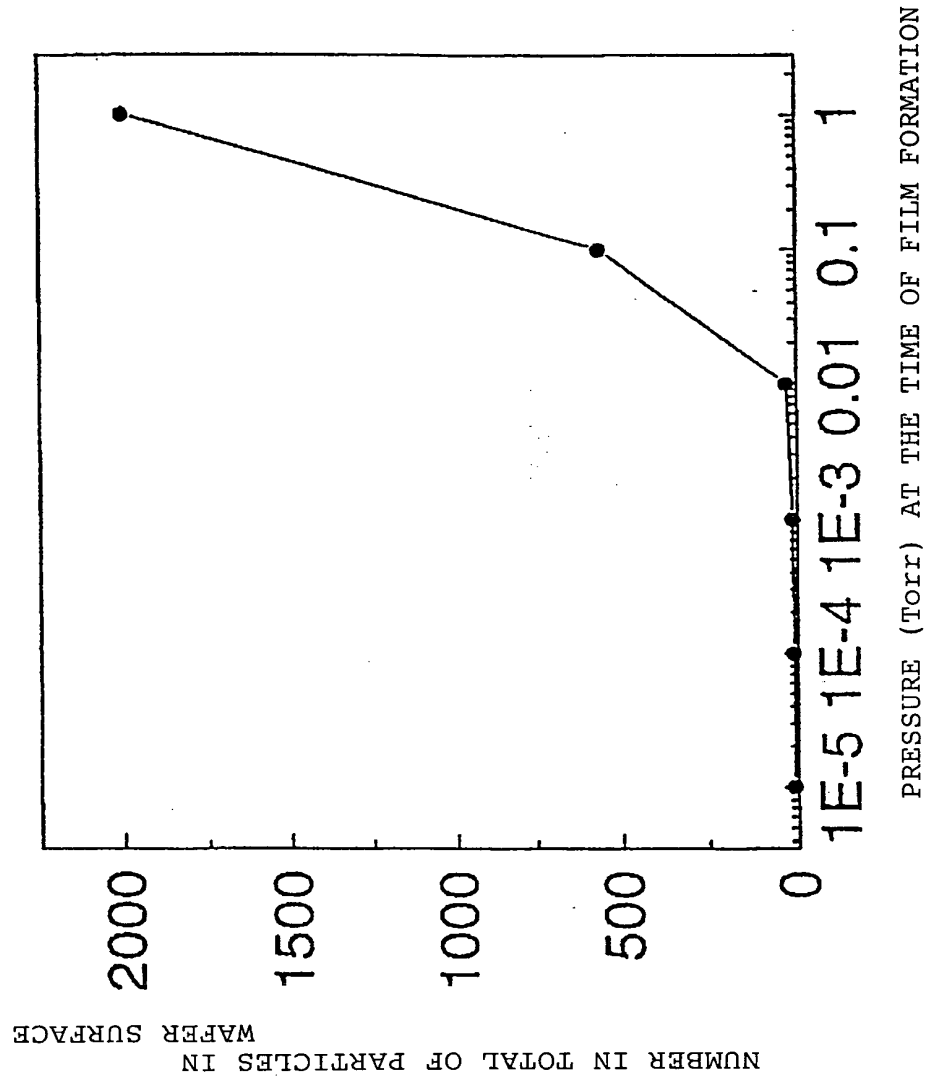


Fig. 21



TOTAL TO 260

Fig. 22



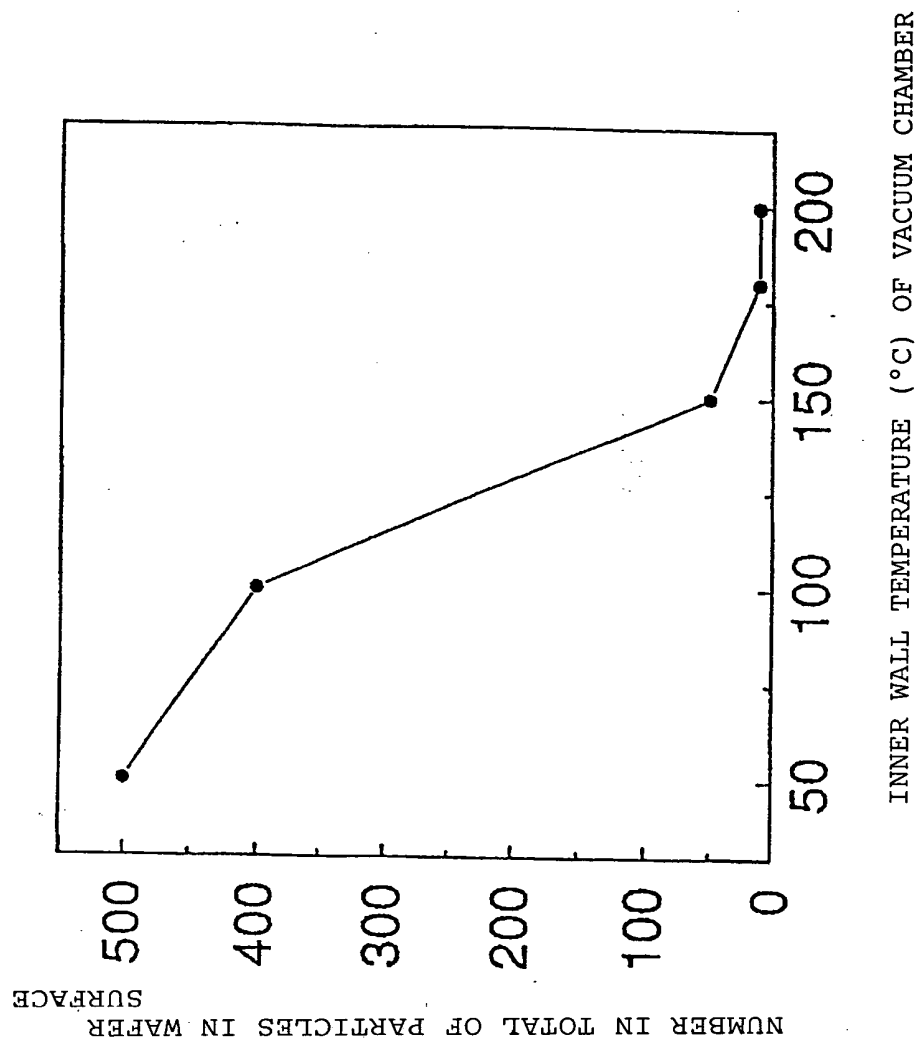


Fig. 24

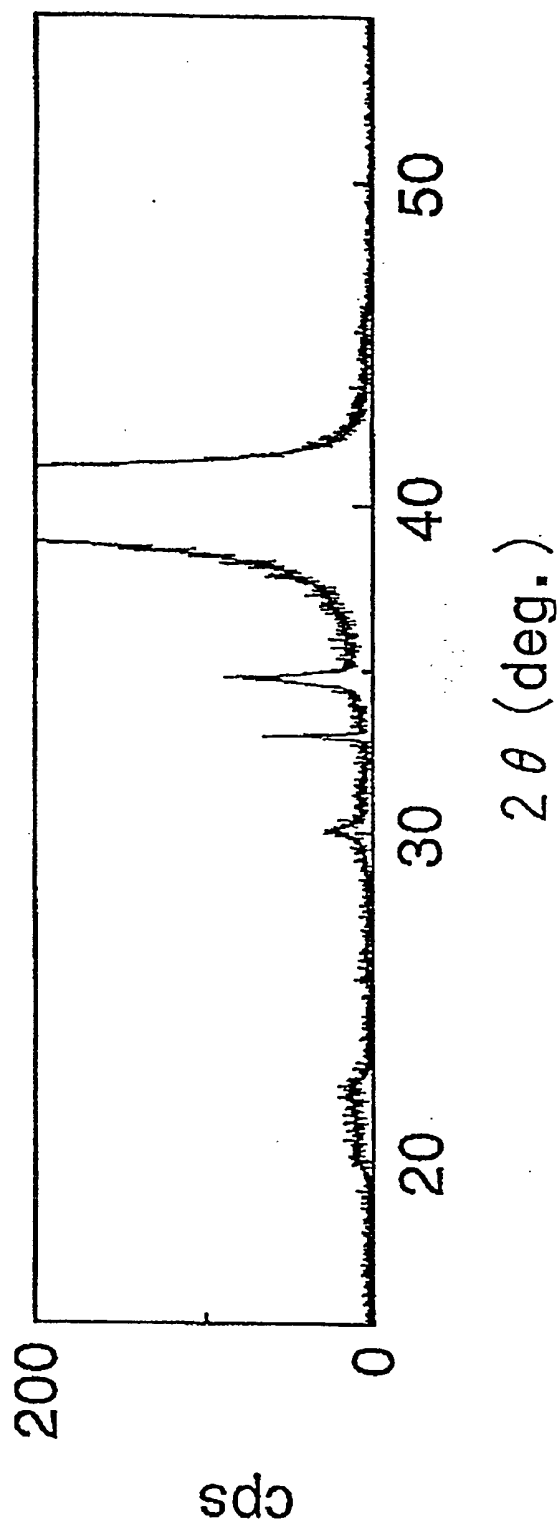




Fig. 25

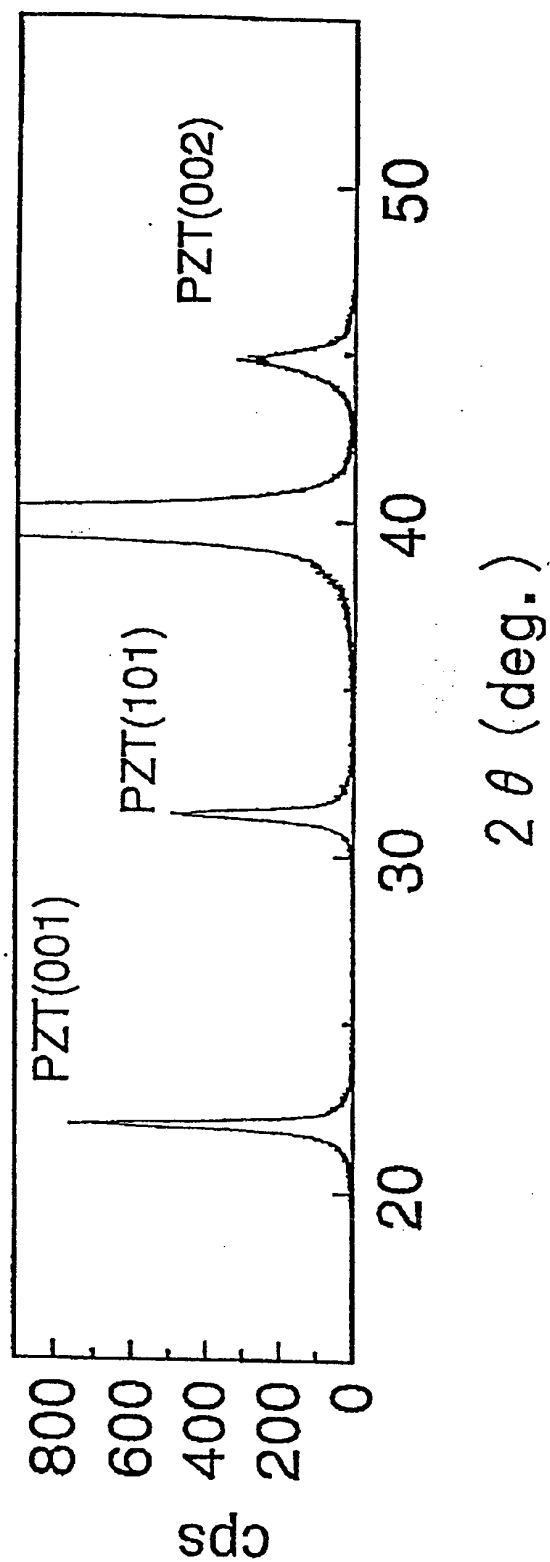


Fig. 26

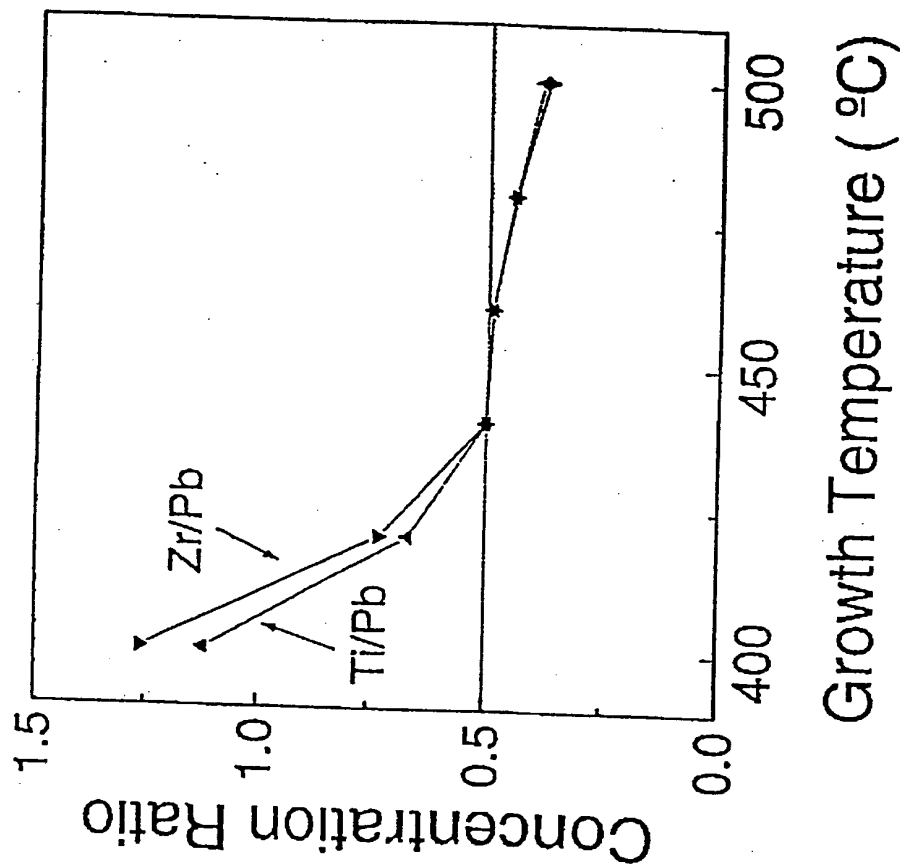


Fig. 27

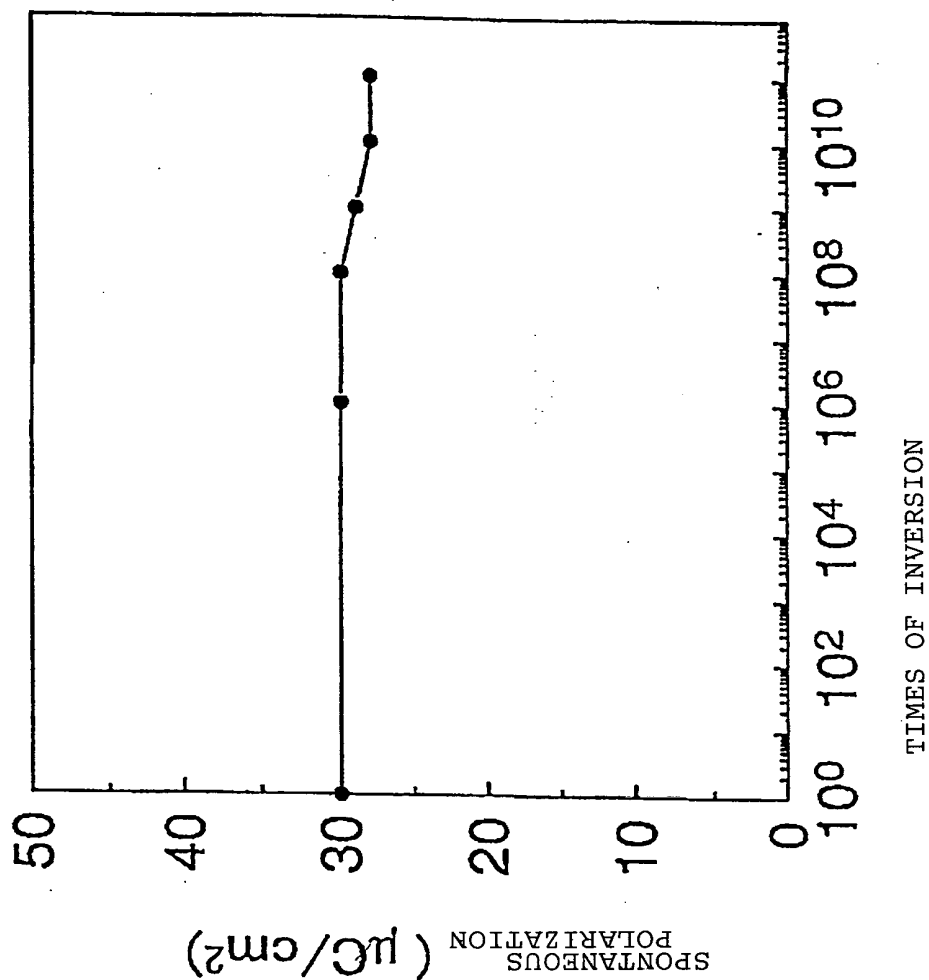


Fig. 28

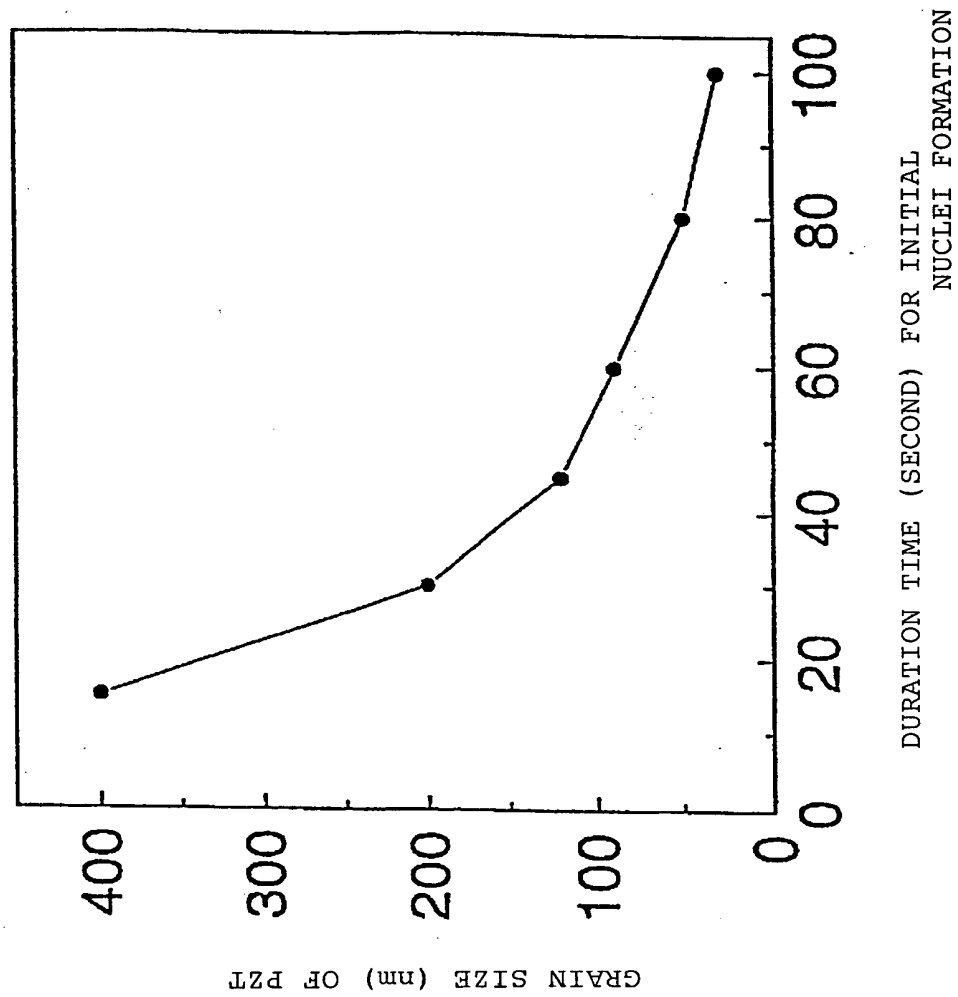


Fig. 29 (A)

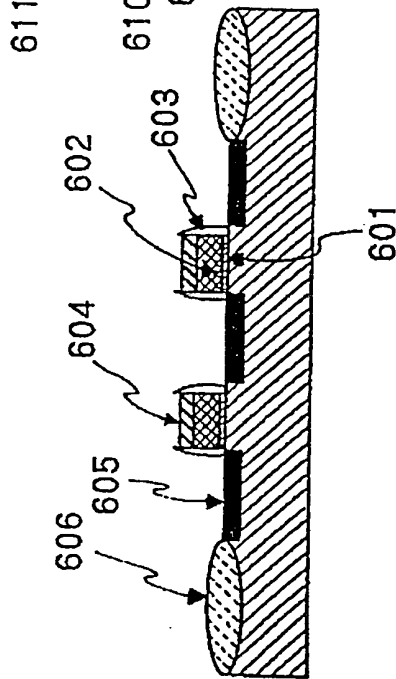


Fig. 29 (B)

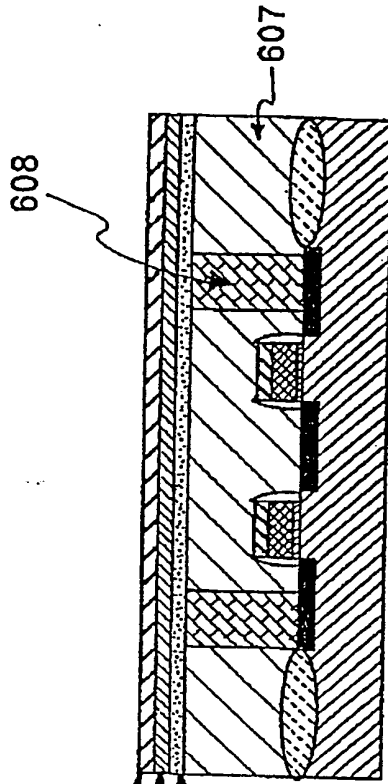


Fig. 29 (C)

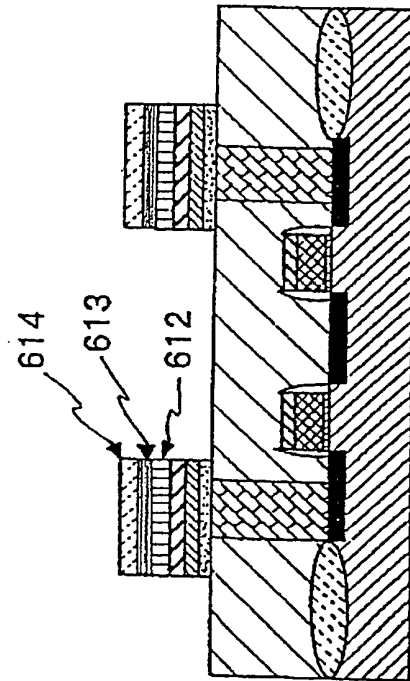
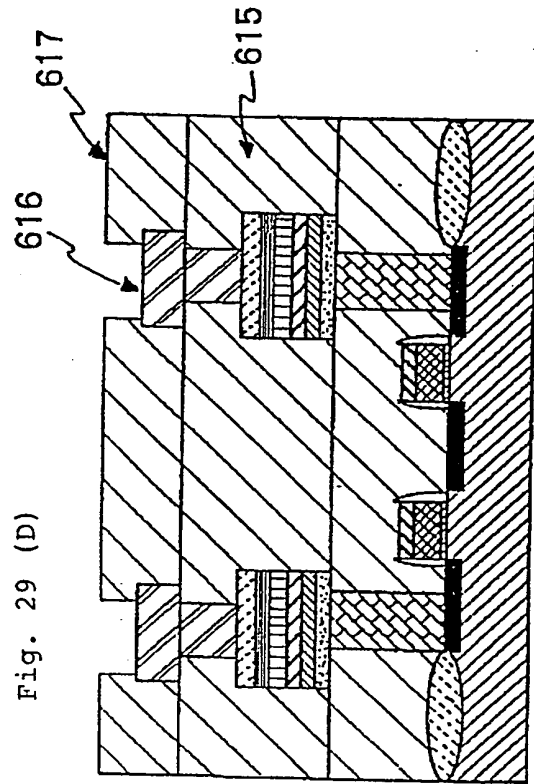


Fig. 29 (D)



A cross-sectional view of a substrate 601 with a thin layer 602. Two openings 603 are formed in the thin layer 602, each filled with a material 604. The openings 603 are separated by a portion of the thin layer 602. Arrows 605 point to the thin layer 602, and arrows 606 point to the openings 603.

Fig. 6 is a cross-sectional view of a semiconductor device. It shows a substrate 607 with a patterned layer 608. A conductive layer 609 is formed on the surface, with openings 610 and 611. A layer 611 is also shown.

A cross-sectional view of a semiconductor device. A substrate with diagonal hatching contains several rectangular regions with different patterns: cross-hatching, dots, and horizontal lines. A layer labeled 612 with a wavy pattern is deposited on top of the substrate, covering the patterned regions and the spaces between them.

Fig. 31 (A)

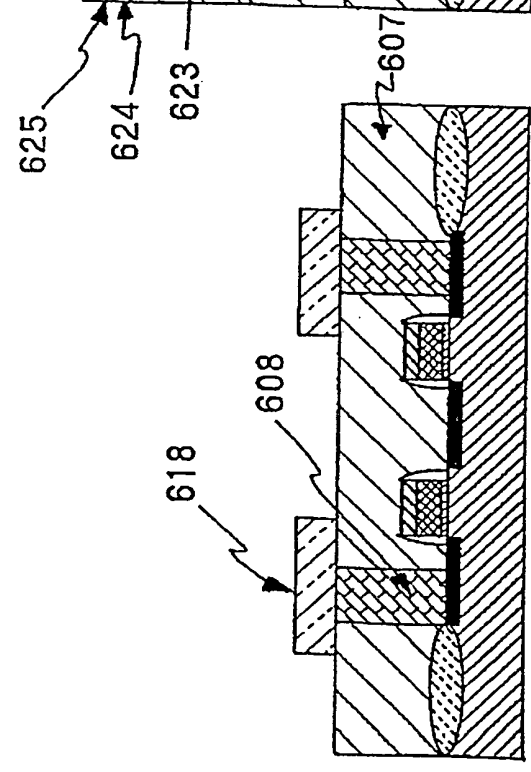


Fig. 31 (B)

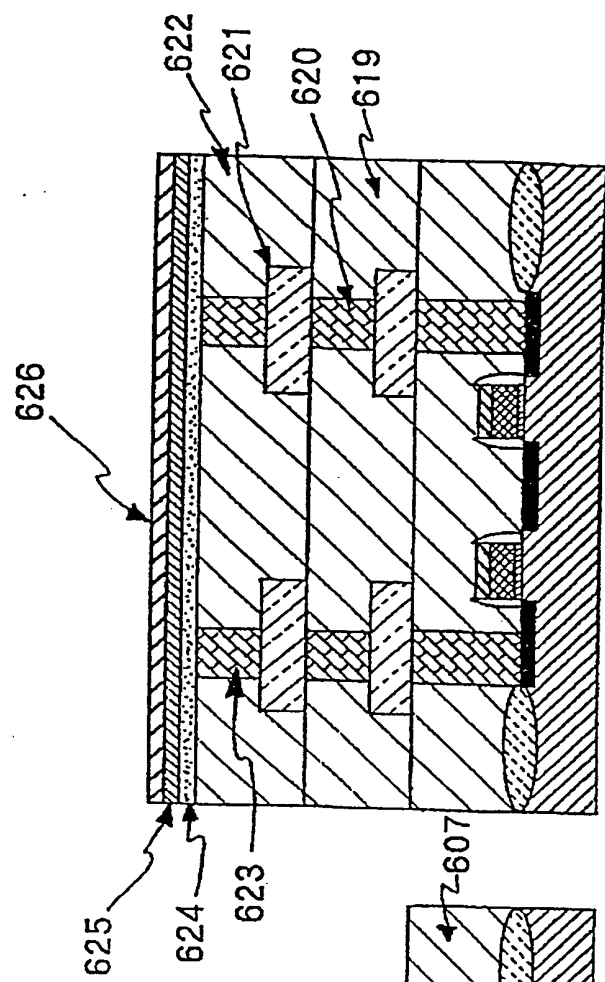


Fig. 32 (C)

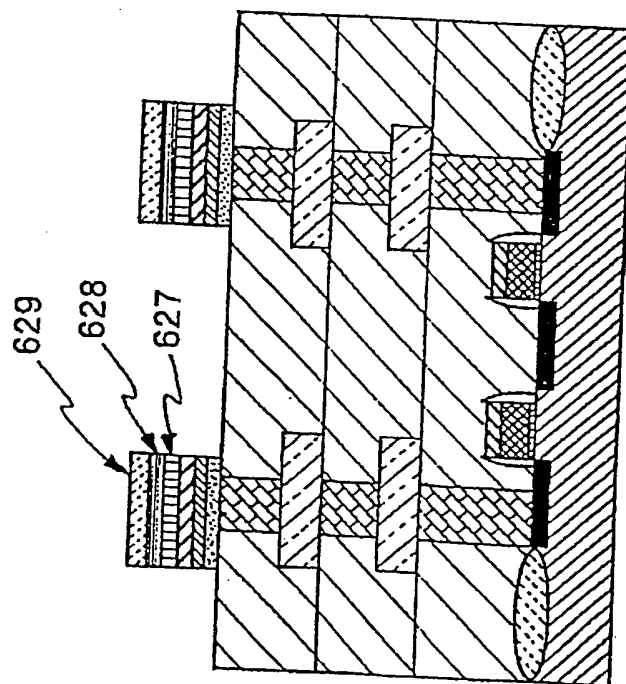


Fig. 32 (D)

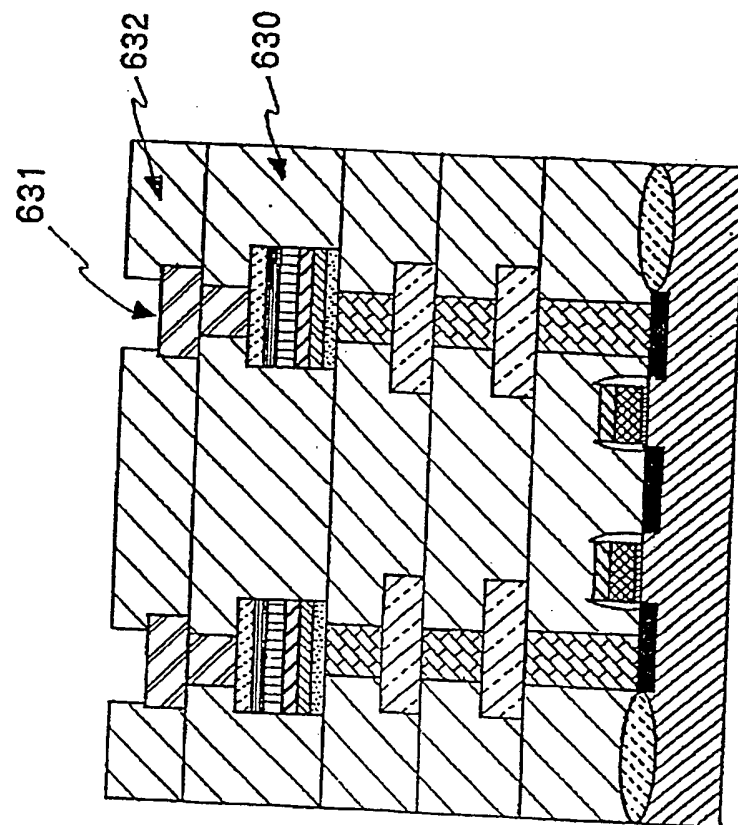




Fig. 33

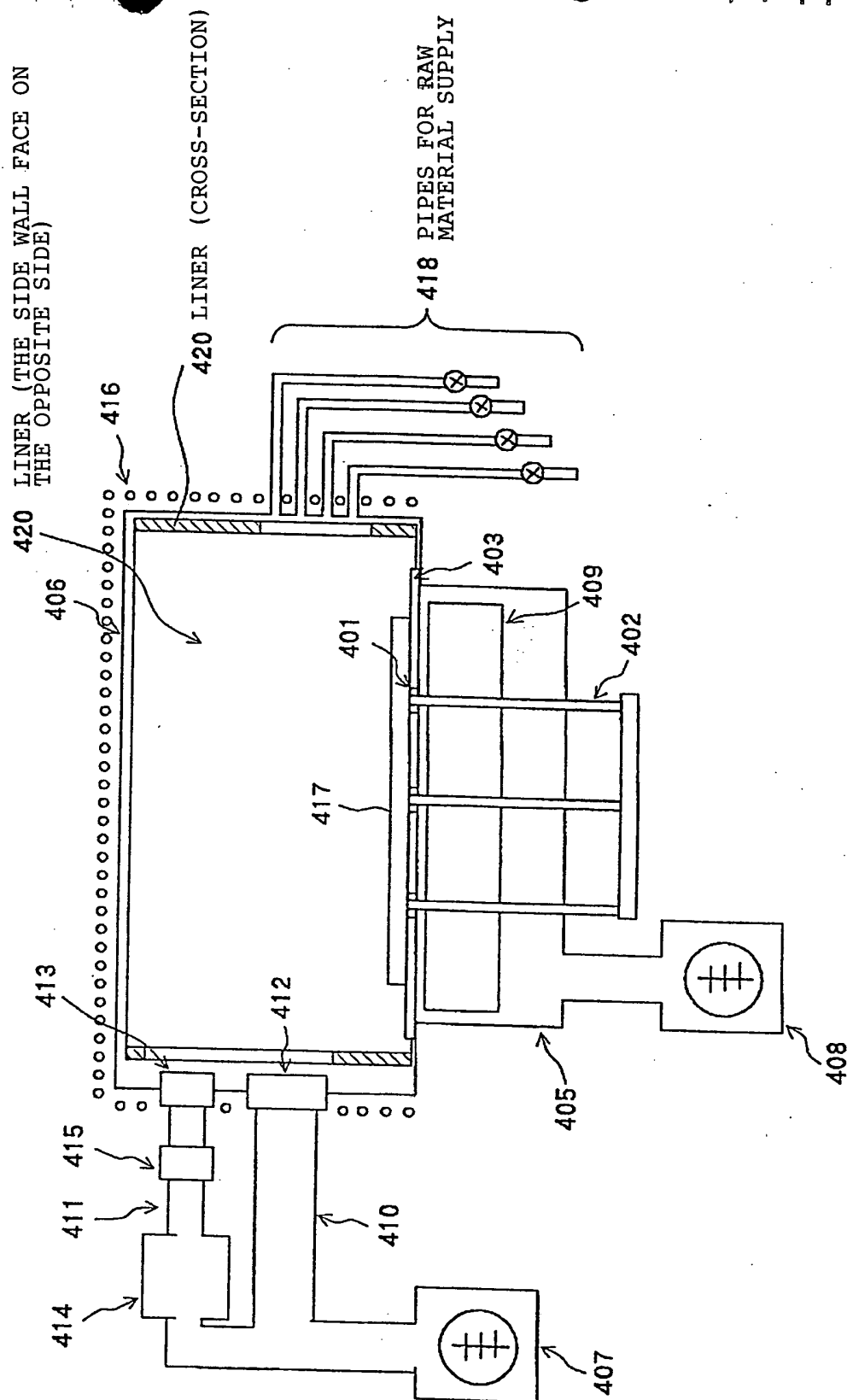


Fig. 34

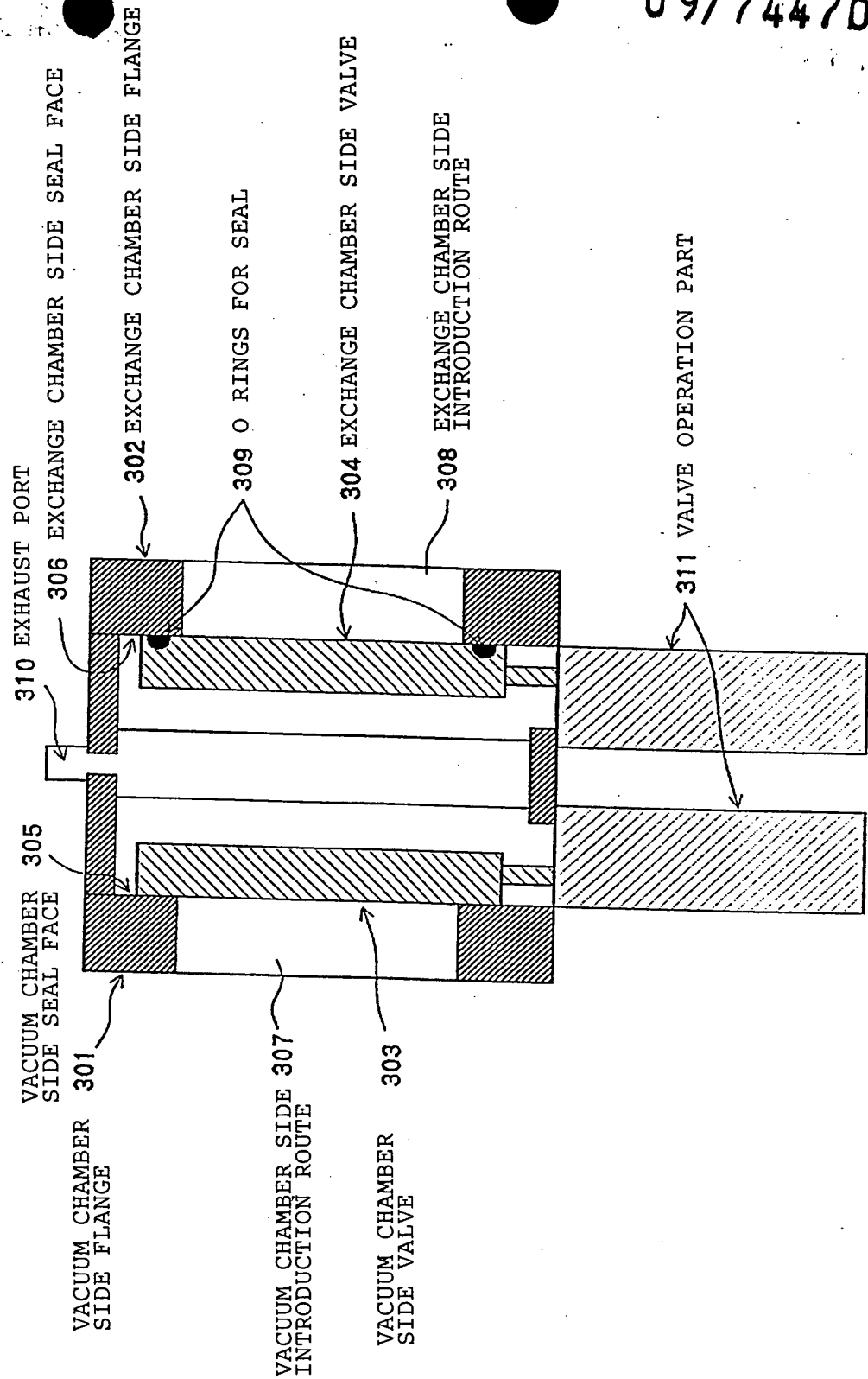
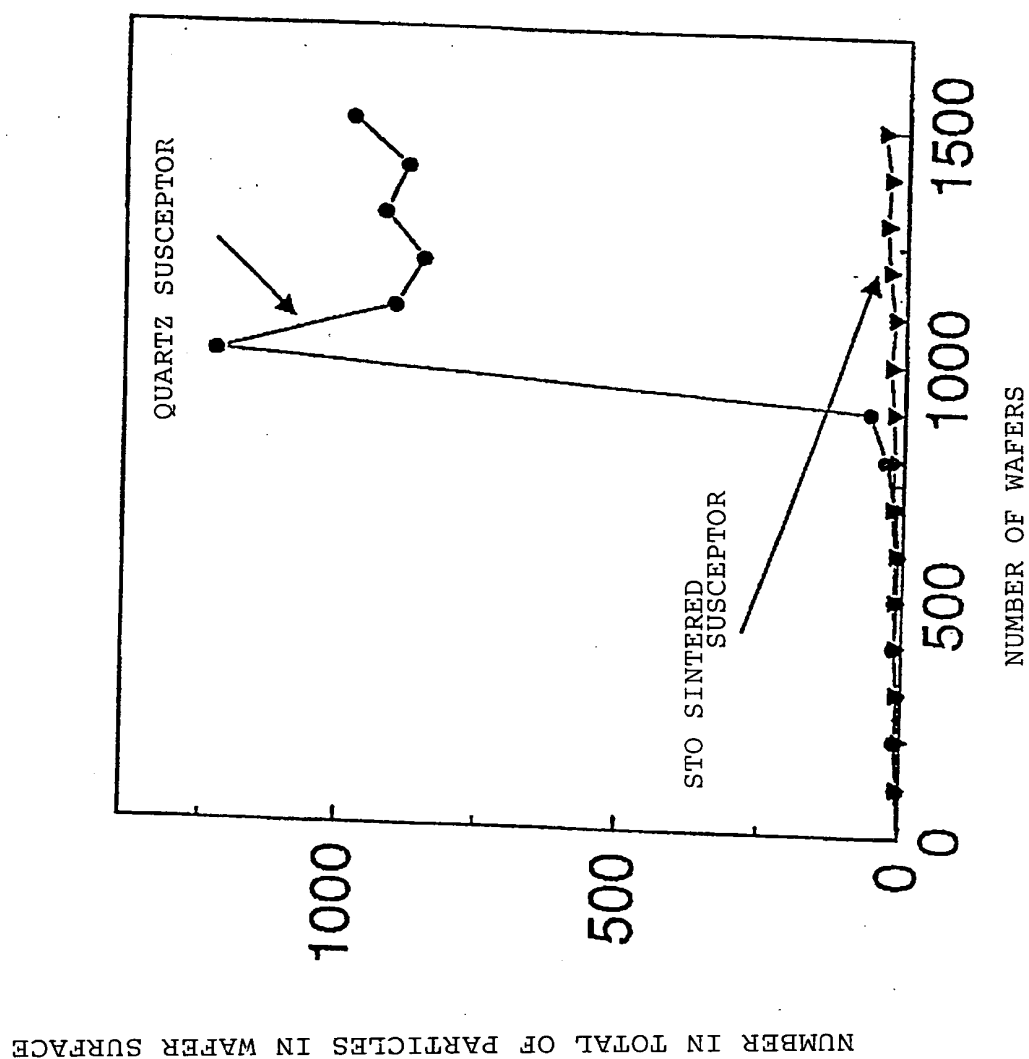


Fig. 35



NUMBER IN TOTAL OF PARTICLES IN WAFER SURFACE

Fig. 36

